Central™
Semiconductor Corp.

PROCESS CPD91V

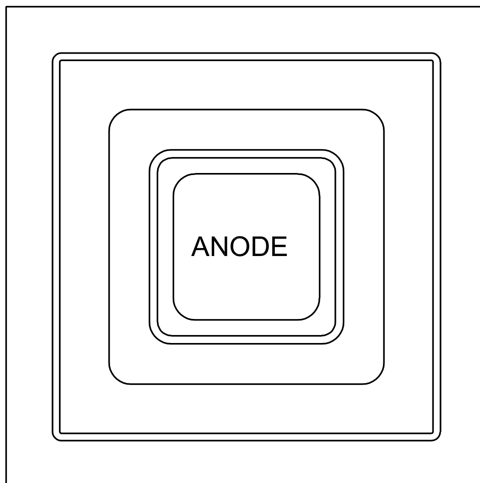
Switching Diode

Low Leakage Switching Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Anode Bonding pad Area	3.4 x 3.4 MILS
Top Side Metalization	Al - 15,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE: CATHODE R0

GROSS DIE PER 4 INCH WAFER
94,130

PRINCIPAL DEVICE TYPES
CMPD6001 Series
CMOD6001
CMLD6001
CMLD6001DO
CMDD6001

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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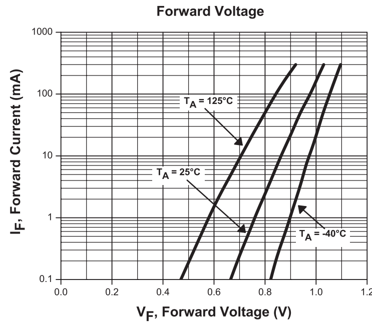
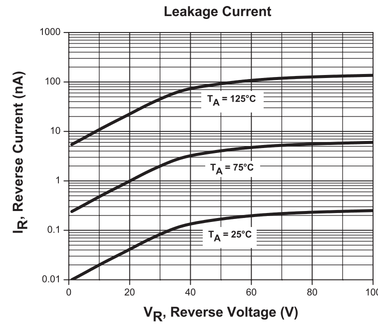
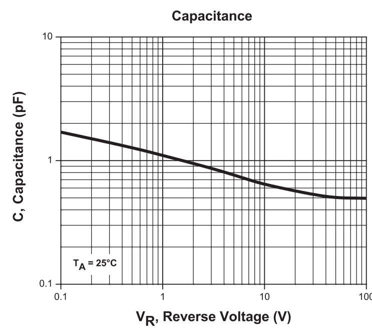
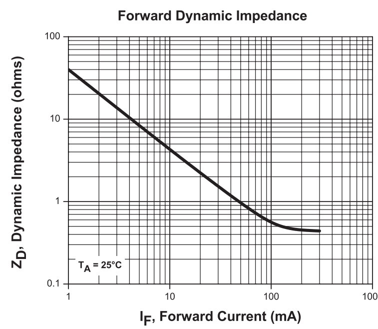
PROCESS CPD91V

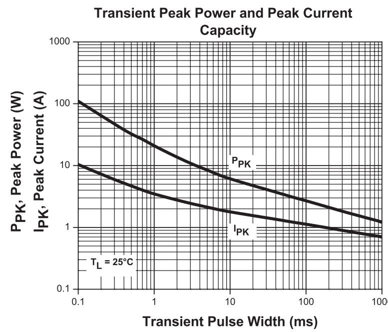
Typical Electrical Characteristics

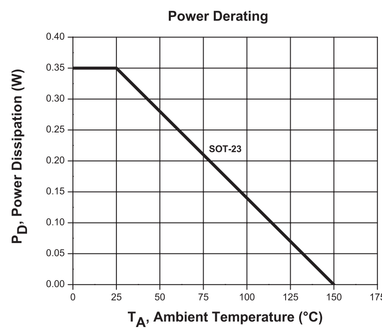












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